

### Description

The FDMS8888 uses advanced trench technology

to provide excellent  $R_{\text{DS}(\text{ON})},$  low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

## **General Features**

V<sub>DS</sub> = 30V I<sub>D</sub> =50A

 $R_{DS(ON)} < 8.5 m\Omega V_{GS} = 10V$ 

## Application

Battery protection

Load switch

Uninterruptible power supply

### Package Marking and Ordering Information

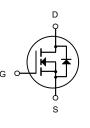
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Product ID	Pack	Brand	Qty(PCS)
FDMS8888	DFN5X6-8L	HXY MOSFET	5000

## Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

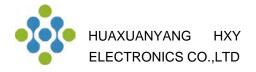
Symbol	Parameter	Rating	Units
Vds	Drain-Source Voltage	V	
Vgs	Gate-Source Voltage	±20	V
l₀@Tc=25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	60	А
l⊳@Tc=100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	38	А
Ідм	Pulsed Drain Current <sup>2</sup>	200	А
EAS	Single Pulse Avalanche Energy <sup>3</sup>	36	mJ
las	Avalanche Current	50	А
P <sub>D</sub> @Tc=25°C	Total Power Dissipation <sup>4</sup>	31	W
Tstg	Storage Temperature Range	Storage Temperature Range -55 to 150	
TJ	Operating Junction Temperature Range	-55 to 150	°C
Reja	Thermal Resistance Junction-Ambient <sup>1</sup>	62	°C/W
Rejc	Thermal Resistance Junction-Case <sup>1</sup>	27	°C/W





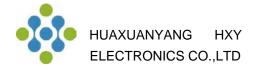


N-Channel MOSFET

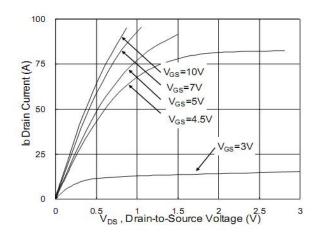


# Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter Conditions		Min	Тур	Max	Units	
BV <sub>DSS</sub>	Drain-Sourtce Breakdown Voltage	ge V <sub>GS</sub> =0V,I <sub>D</sub> =250 μ A				v	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>GS</sub> =0V, V <sub>DS</sub> =24V			1	μA	
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ =±20V, $V_{DS}$ =0A			±100	nA	
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}$ = $V_{DS}$ , $I_D$ =250 $\mu$ A		1.5	2.5	v	
_	2	V <sub>GS</sub> =10V,I <sub>D</sub> =30A		6.5 8.5			
R <sub>DS(ON)</sub>	Drain-Source On Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V,I <sub>D</sub> =15A		11	14	mΩ	
G <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =30A		38		S	
C <sub>iss</sub>	Input Capacitance			1317	1844	pF	
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz		163	228		
C <sub>rss</sub>	Reverse Transfer Capacitance			131	183		
t <sub>d(on)</sub>	Turn-On Delay Time			4.6	9.2	ns	
t,	RiseTime	V <sub>DD</sub> =15V,I <sub>D</sub> =15A,R <sub>L</sub> =Ω		12.2	22	ns	
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>GS</sub> =15V,R <sub>G</sub> =3.3Ω		26.6	53	ns	
t <sub>f</sub>	FallTime			8	16	ns	
Qg	Total Gate Charge			21	17.6	nC	
$\mathbf{Q}_{gs}$	Gate-Source Charge	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =15V,		2.35	5.9	nC	
$\mathbf{Q}_{gd}$	Gate-Drain "Miller" Charge	I <sub>D</sub> =15A		5.9	7.1	nC	
V <sub>SD</sub>	Source-Drain Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V,I <sub>S</sub> =1A			1	v	
IS	Continuous Source Current1.5	VG=VD=0V , Force			58	А	
ISM	Pulsed Source Current 2.5	Current			115	А	
trr	Reverse Recovery Time	IF=30A,		9.2			
Qrr	Reverse Recovery Charge	dI/dt=100A/¦ÌsTJ=25°C		2			



## **Typical Characteristics**



### Fig.1 Typical Output Characteristics

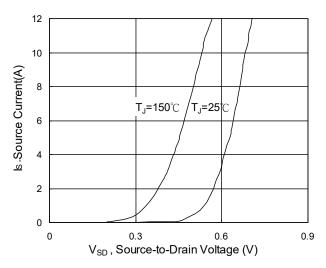


Fig.3 Forward Characteristics of reverse

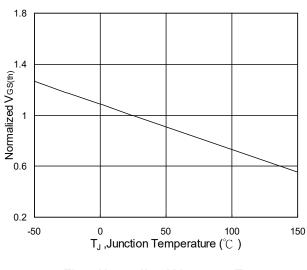


Fig.5 Normalized V<sub>GS(th)</sub> vs. T<sub>J</sub>

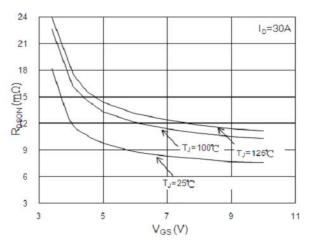


Fig.2 On-Resistance vs. Gate-Source

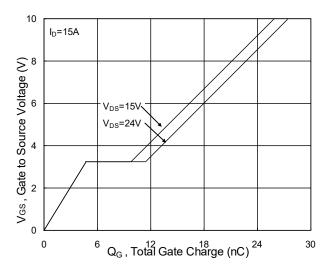
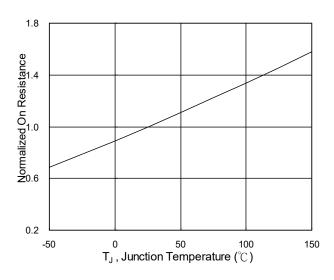


Fig.4 Gate-Charge Characteristics







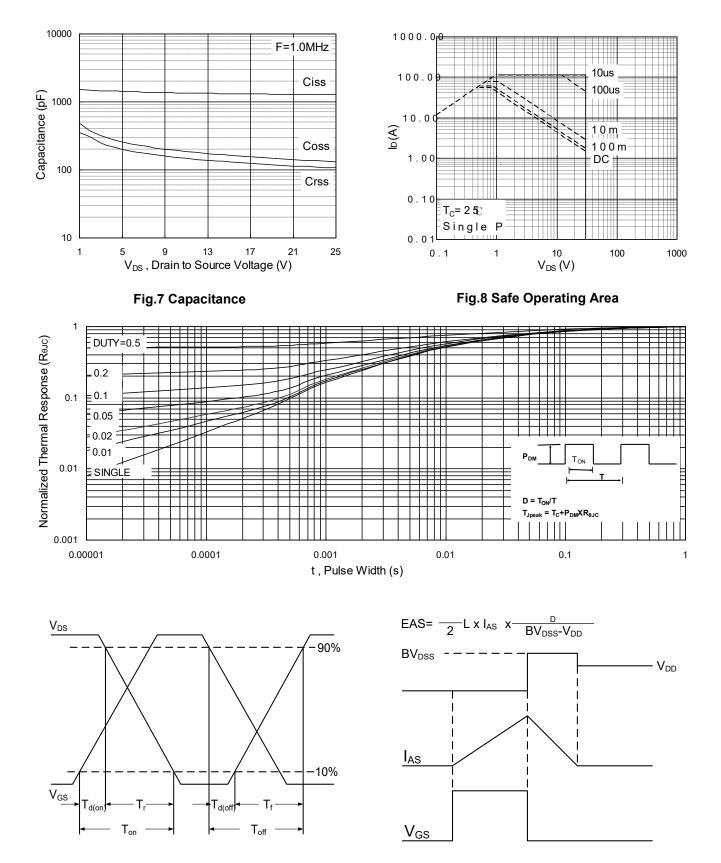
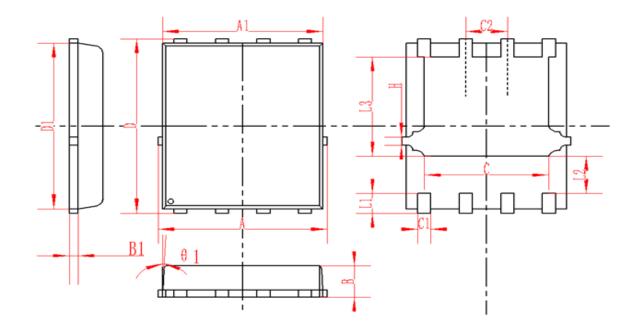


Fig.10 Switching Time Waveform



# DFN5X6-8L Package Information



SYMBOL		MM			INCH	
	MIN	NOM	MAX	MIN	NOM	MAX
А	5.3	5.5	5.7	0.208	0.216	0.224
A1	5.1	5.2	5.3	0.2	0.204	0.209
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.85	6.05	6.25	0.23	0.238	0.246
В	0.85	0.95	1.05	0.033	0.037	0.041
B1	0.254REF		0.010REF			
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2		1.27TYP			0.5TYP	
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010



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